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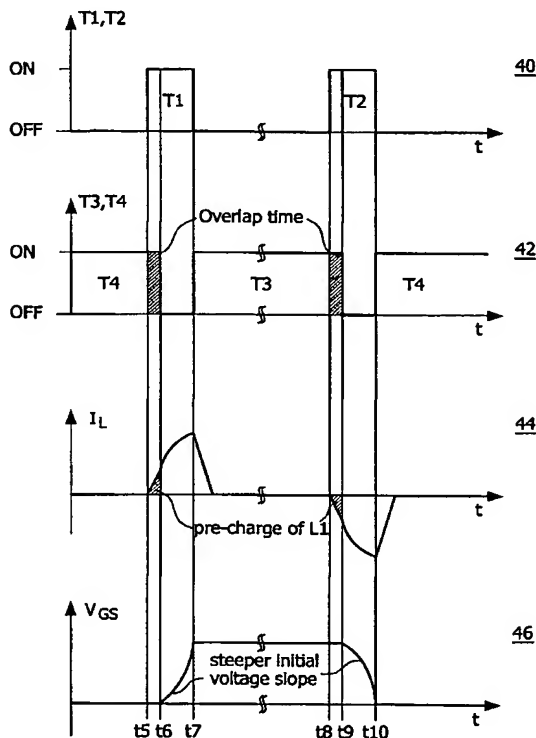
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(54) Title: HIGH FREQUENCY CONTROL OF A SEMICONDUCTOR SWITCH



(57) Abstract: Resonant gate driver circuits provide for an efficient switching of, for example, a MOSFET. However, often an operation of the resonant gate driver circuit does not allow for an application where high switching frequencies are required. According to the present invention, a pre-charging of the inductor of the resonant gate drive circuit is performed. This allows for a highly energy efficient and fast operation of the MOSFET.



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